AZ® Remover 920 photoresist stripper is designed for fast delamination and dissolution of photoresist patterns while maintaining broad compatibility with device substrates and metal films. Merck’s proprietary solvent and additive blend is environmentally friendly and fully compliant with the European Union’s REACH regulatory code.

**APPLICATIONS**
- Bulk Photoresist Removal
- Metal Lift-off Lithography
- Cu Pillar Metallization Cleans
- RDL Metallization Cleans
- Delamination of Heavily Cured Photoresist Patterns & Organic Residues

**DEVICE COMPATIBILITY**
- **Substrates**
  - Si, SiO2, GaAs
- **Metals**
  - Al, Cu, Ti, W, TiW, TiN, Sn, Ni
- **Insulators**
  - TEOS, SiO2, SiN, SiON

**POLYMER REMOVAL**
- Full Dissolution & Delamination
  - DNQ/Novolac Positive Photoresists (AZ® P4620)
  - Chemically Amplified Positive Photoresists (AZ® 3DT)
- Fast Delamination
  - Chemically Amplified Negative Tone PR (AZ® 15nxt, AZ® nLOF & AZ® ANR series)

**CHEMICAL PROPERTIES**
- Organic solvent based with amine additives
- EHS Friendly - NMP, DMAC & TMAH free
- Alkaline pH
- High boiling point of 188°C, low evaporation
- Flash point of 84.4°C

**REMOVAL PROCESSING CONDITIONS**
- AZ® Remover 920 is fully water miscible and can go directly to DIW rinse.
- IPA or alternate intermediate rinse solvent can also be used.
- Recommended operating temperature is 60°C to 80°C.
- Suitable for use on wet bench, batch-spray, soak & spray, or single-wafer spray tooling.
- Compatible with PTFE, HDPE, 316L EP Stainless Steel & Quartz. Incompatible with Viton.
Removal of AZ® P4620 Photore sist

- Substrate: 8” Silicon
- Film Tks: 12.6 μm
- Exposure: i-line 600 mJ/cm²
- Soft Bake: 110°C/240sec
- PEB: none
- Development: AZ® 300MIF 4 x 60sec
- Remover Bath: 80°C / 5min soak

Removal of AZ® 3DT Photore sist

- Substrate: 8” Silicon
- Film Tks: 12.6 μm
- Exposure: i-line 400 mJ/cm²
- Soft Bake: 110°C/300sec
- PEB: none
- Development: AZ® 300MIF 2 x 60sec
- Remover Bath: 80°C / 5min soak

Removal of AZ® NLOF2070 Photore sist

- Substrate: 8” Silicon
- Film Tks: 7.8 μm
- Exposure: i-line 2200 mJ/cm²
- Soft Bake: 110°C/90sec
- PEB: 110°C/90sec
- Development: AZ® 300MIF 1 x 90sec
- Remover Bath: 80°C / 5min soak

Removal of AZ® 15NXT Photore sist

- Substrate: 8” Silicon
- Film Tks: 11.2 μm
- Exposure: i-line 900 mJ/cm²
- Soft Bake: 110°C/180sec
- PEB: 120°C/60sec
- Development: AZ® 300MIF 2 x 60sec
- Remover Bath: 80°C / 5min soak

DISCLAIMER

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